

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("3254234").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/30 12:25
S2	425	"257"/\$.ccls. and (varactor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/30 14:57
S3	2	("6100770").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/30 13:01
S4	157	(257/595).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/30 13:09
S5	39	(257/598).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/30 13:23
S6	82	(257/601).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/30 13:53
S7	102	(257/596).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/02 09:48
S8	74	(257/602).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/30 14:00

S9	124	(257/312).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/30 14:03
S10	172	(257/313).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/30 14:06
S11	90	(438/379).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/01/30 14:06
S12	662	"257"/\$.ccls. and ((capacitor) with (inductor))	USPAT	OR	OFF	2004/01/30 14:58
S13	4	"257"/\$.ccls. and (capacitor near connected near (inductor))	USPAT	OR	OFF	2004/01/30 15:00
S14	533	"257"/\$.ccls. and ((second adj gate) with (second adj conductivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/02 14:16
S15	6	"257"/\$.ccls. and ((semiconductor adj gate adj electrode) with (second adj conductivity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/02 14:19
S16	4	"257"/\$.ccls. and ((semiconductor adj gate adj electrode) with (concentration))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/02 14:20
S17	153	"257"/\$.ccls. and ((semiconductor adj gate adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/02 14:57
S18	170	(257/407).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/02 15:23
S19	82	"257"/\$.ccls. and (poly\$1crystalline adj gate adj electrode)	USPAT	OR	OFF	2004/02/02 15:26

S20	1	"257"/\$.ccls. and ((poly\$1crystalline adj gate adj electrode) with (advantag\$4))	USPAT	OR	OFF	2004/02/02 15:26
S22	206	(361/277,332).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/30 15:11
S23	206	(361/277).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/30 15:11
S24	376	(361/281,292).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 16:38
S25	564	(257/595-602).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 11:16
S26	1667	MIS with capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 17:06
S27	853	"257"/\$.ccls. and (MIS with capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/01 17:06
S28	564	(257/595-602).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 10:44
S29	734	(361/277,332,136,281,292).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 11:56
S30	5391	national adj semiconductor adj corporation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 11:57

S31	3088	national adj semiconductor adj corporation.asn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 11:57
S32	941	national adj semiconductor adj corporation.asn. and (capacitor or varactor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 12:36
S33	34	BULUCEA near CONSTANTIN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/03 12:00
S34	1206	varactor	US-PGPUB	OR	OFF	2005/10/03 12:00
S35	5552	varactor	US-PGPUB; USPAT	OR	OFF	2005/10/03 12:00